

## R-C Thermal Model Parameters

### DESCRIPTION

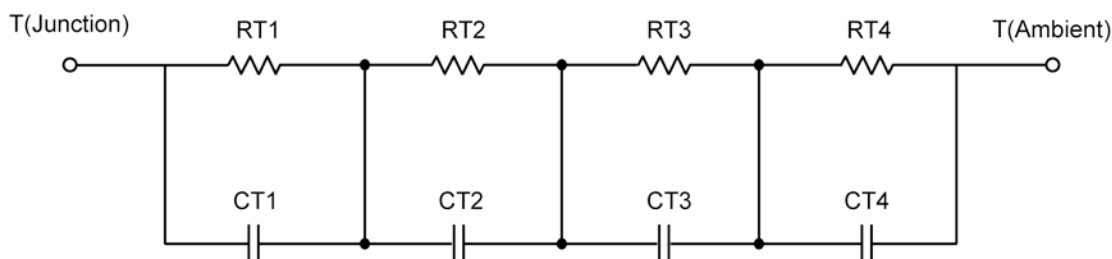
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

*For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).*

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	N/A	9.5991 m	N/A
RT2	N/A	213.0527 m	N/A
RT3	N/A	757.4802 m	N/A
RT4	N/A	119.8681 m	N/A
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	N/A	36.3494	N/A
CT2	N/A	3.6982 m	N/A
CT3	N/A	51.0100 m	N/A
CT4	N/A	1.0734	N/A

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*



## R-C THERMAL MODEL FOR FILTER CONFIGURATION



<b>R-C VALUES FOR FILTER CONFIGURATION</b>			
<b>Thermal Resistance (°C/W)</b>			
<b>Junction to</b>	<b>Ambient</b>	<b>Case</b>	<b>Foot</b>
RF1	N/A	244.1208 m	N/A
RF2	N/A	404.4692 m	N/A
RF3	N/A	402.3555 m	N/A
RF4	N/A	49.0545 m	N/A
<b>Thermal Capacitance (Joules/°C)</b>			
<b>Junction to</b>	<b>Ambient</b>	<b>Case</b>	<b>Foot</b>
CF1	N/A	3.5520 m	N/A
CF2	N/A	45.9469 m	N/A
CF3	N/A	297.4549 u	N/A
CF4	N/A	4.4737	N/A

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

